

$V_{CE} = 650\text{ V}$, $I_C = 15\text{ A}$
Trench Field Stop IGBTs with Fast Recovery Diode
FGF65A3L6L

Description

FGF65A3L6L is 650 V / 15 A Field Stop IGBT. Sanken original trench structure decreases gate capacitance, and achieves low saturation voltage and switching losses reduction. Thus, the Field Stop IGBT can improve the efficiency of your circuit.

Package

TO3PF-3L

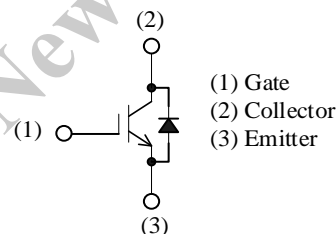
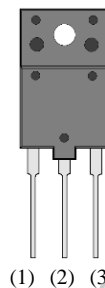
Features

- Low Saturation Voltage
- High Speed Switching
- With Integrated Fast Recovery Diode
- Bare lead frame: Pb-free (RoHS compliant)

- V_{CE} ----- 650 V
- I_C ($T_C = 100\text{ }^\circ\text{C}$)----- 15 A
- Short Circuit Withstand Time ----- 5 μs
- $V_{CE(sat)}$ ----- 1.60 V typ.
- t_f ($T_J = 175\text{ }^\circ\text{C}$) ----- 160 ns typ.
- V_F ----- 1.5 V typ.

Applications

- Uninterruptible Power Supply (UPS)
- Inverter Circuit
- Bridge Circuit



Not to scale

Not Recommended for New Designs

FGF65A3L6L

Absolute Maximum Ratings

Unless otherwise specified, $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Rating	Unit	Remarks
Collector to Emitter Voltage	V_{CE}		650	V	
Gate to Emitter Voltage	V_{GE}		± 30	V	
Continuous Collector Current ⁽¹⁾	I_C	$T_C = 25\text{ }^\circ\text{C}$	25	A	
		$T_C = 100\text{ }^\circ\text{C}$	15	A	
Pulsed Collector Current	$I_{C(PULSE)}$	$PW \leq 1\text{ ms}$, $duty\ cycle \leq 1\%$	90	A	
Diode Continuous Forward Current ⁽¹⁾	I_F	$T_C = 25\text{ }^\circ\text{C}$	30	A	
		$T_C = 100\text{ }^\circ\text{C}$	20	A	
Diode Pulsed Forward Current	$I_{F(PULSE)}$	$PW \leq 1\text{ ms}$, $duty\ cycle \leq 1\%$	90	A	
Short Circuit Withstand Time	t_{SC}	$V_{GE} = 15\text{ V}$, $V_{CE} = 400\text{ V}$ $T_J = 175\text{ }^\circ\text{C}$	5	μs	
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	72	W	
Operating Junction Temperature	T_J		175	$^\circ\text{C}$	
Storage Temperature Range	T_{STG}		-55 to 150	$^\circ\text{C}$	
Isolation Voltage (RMS)	$V_{ISO(RMS)}$	⁽²⁾	1500	V	
Isolation Voltage	$V_{ISO(RMS)}$	Between surface of case and all pins that are shorted; AC, 60 Hz, 1 min	1500	V	

Thermal Characteristics

Unless otherwise specified, $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	Remarks
Thermal Resistance of IGBT (Junction to Case)	$R_{\theta JC(IGBT)}$		—	—	2.08	$^\circ\text{C/W}$	
Thermal Resistance of Diode (Junction to Case)	$R_{\theta JC(Di)}$		—	—	2.28	$^\circ\text{C/W}$	

⁽¹⁾ I_C and I_F are determined by the maximum junction temperature for TO3P-3L package.

⁽²⁾ Between surface of the device and each pin; AC, 60 Hz, 1 min.

FGF65A3L6L

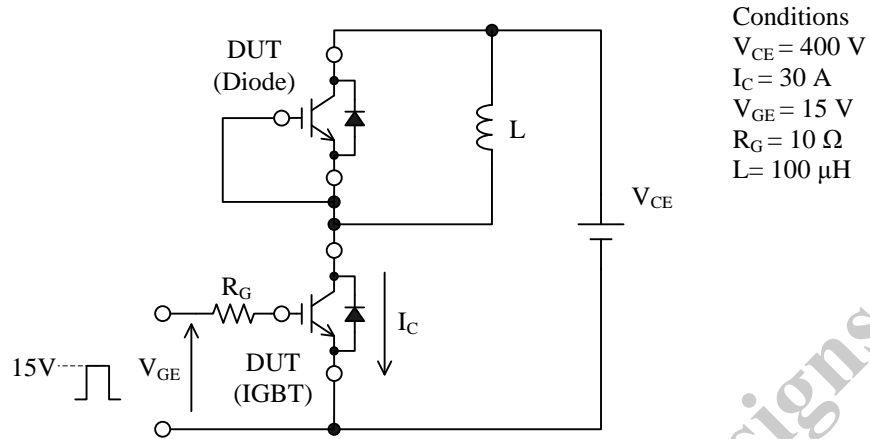
Electrical Characteristics

Unless otherwise specified, $T_A = 25\text{ }^\circ\text{C}$

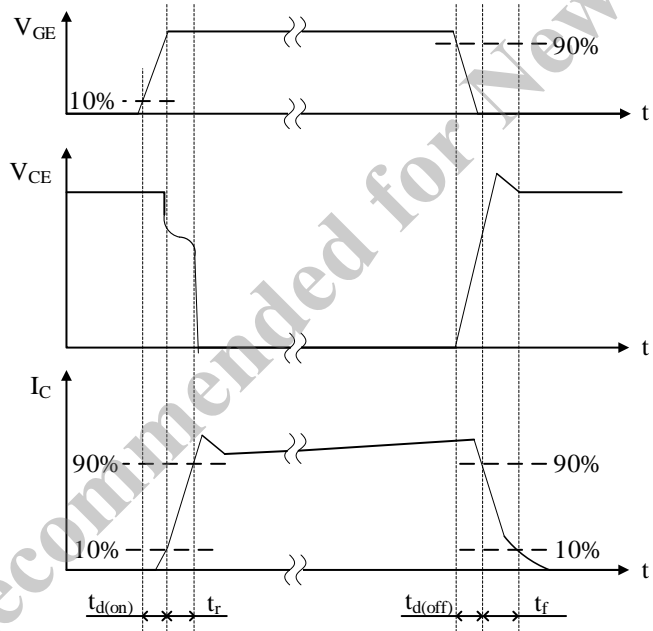
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Collector to Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 100\text{ }\mu\text{A}$, $V_{GE} = 0\text{ V}$	650	—	—	V	
Collector to Emitter Leakage Current	I_{CES}	$V_{CE} = 650\text{ V}$, $V_{GE} = 0\text{ V}$	—	—	100	μA	
Gate to Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 30\text{ V}$	—	—	± 500	nA	
Gate Threshold Voltage	$V_{GE(TH)}$	$V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	4.0	5.5	7.0	V	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}$, $I_C = 30\text{ A}$	—	1.60	1.96	V	
Input Capacitance	C_{ies}	$V_{CE} = 20\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1.0\text{ MHz}$,	—	1800	—	pF	
Output Capacitance	C_{oes}		—	200	—		
Reverse Transfer Capacitance	C_{res}		—	80	—		
Gate charge	Q_g	$V_{CE} = 520\text{ V}$, $I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$	—	60	—	nC	
Turn-on Delay Time	$t_{d(on)}$	$T_J = 25\text{ }^\circ\text{C}$, see Figure 1.	—	30	—	ns	
Rise Time	t_r		—	30	—		
Turn-off Delay Time	$t_{d(off)}$		—	90	—		
Fall Time	t_f		—	40	—		
Turn-on Energy ⁽³⁾	E_{on}		—	0.6	—		mJ
Turn-off Energy	E_{off}	—	0.6	—			
Turn-on Delay Time	$t_{d(on)}$	$T_J = 175\text{ }^\circ\text{C}$, see Figure 1.	—	30	—	ns	
Rise Time	t_r		—	30	—		
Turn-off Delay Time	$t_{d(off)}$		—	120	—		
Fall Time	t_f		—	160	—		
Turn-on Energy ⁽³⁾	E_{on}		—	1.1	—		mJ
Turn-off Energy	E_{off}		—	1.1	—		
Emitter to Collector Diode Forward Voltage	V_F	$I_F = 30\text{ A}$	—	1.5	—	V	
Emitter to Collector Diode Reverse Recovery Time	t_{rr}	$I_F = 30\text{ A}$, $di/dt = 700\text{ A}/\mu\text{s}$	—	70	—	ns	

⁽³⁾ Energy losses include the reverse recovery of diode.

Test Circuits and Waveforms



(a) Test Circuit



(b) Waveform

Figure 1. Test Circuits and Waveforms of dv/dt and Switching Time

Rating and Characteristic Curves

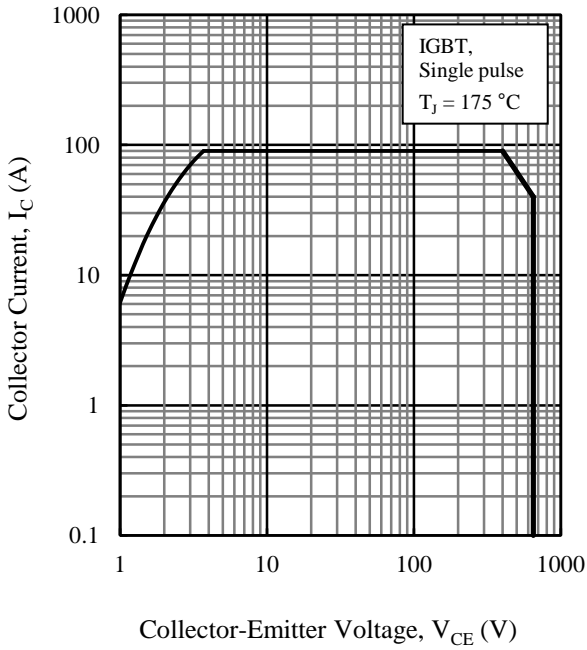


Figure 2. IGBT Reverse Bias Safe Operating Area

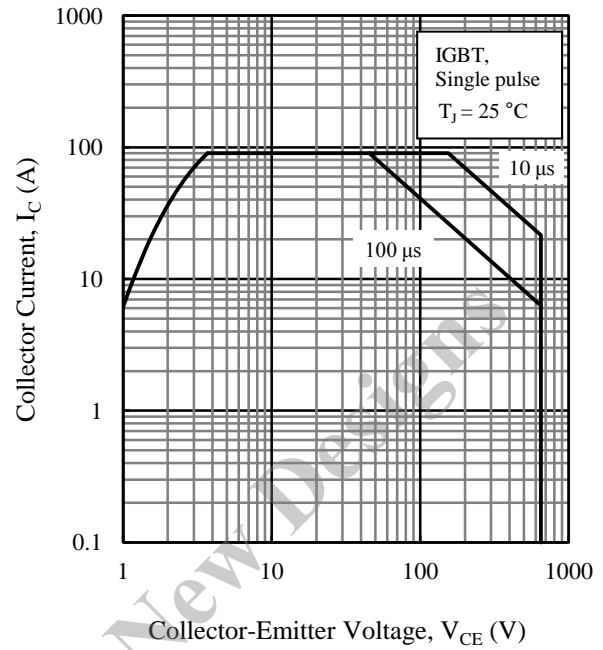


Figure 3. IGBT Safe Operating Area

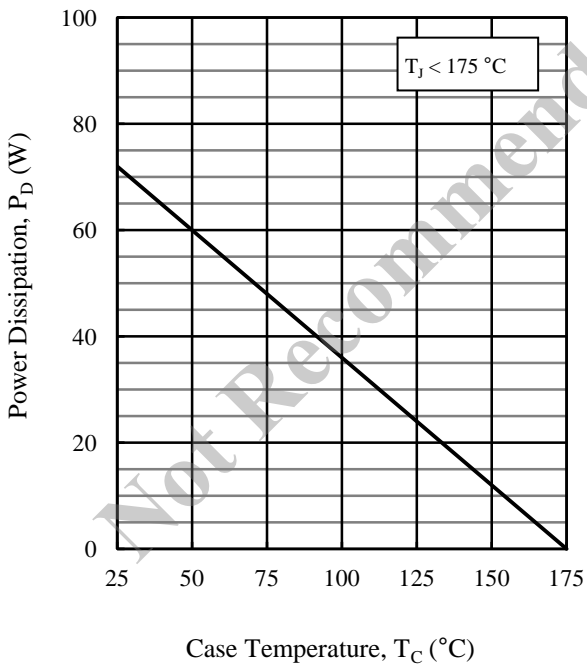


Figure 4. Power Dissipation vs. Case Temperature

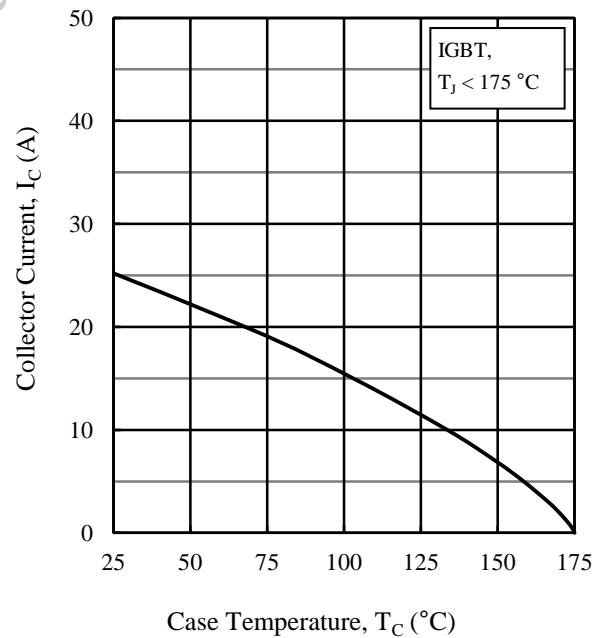


Figure 5. Collector Current vs. Case Temperature

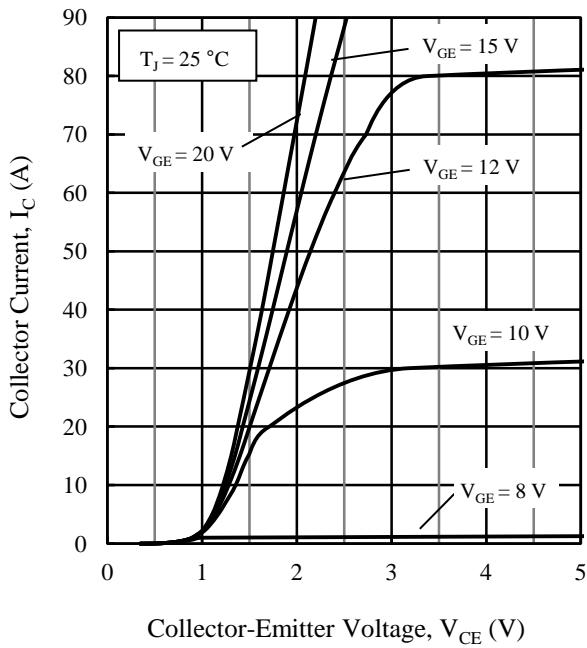


Figure 6. Output Characteristics ($T_J = 25\text{ }^\circ\text{C}$)

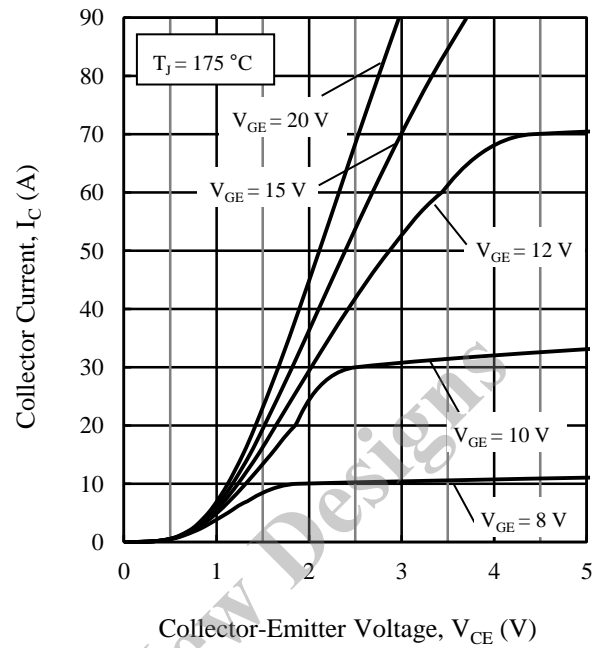


Figure 7. Output Characteristics ($T_J = 175\text{ }^\circ\text{C}$)

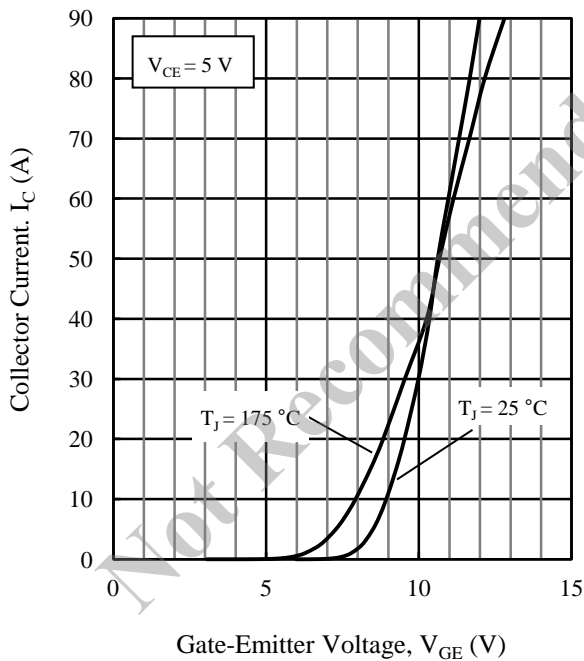


Figure 8. Transfer Characteristics

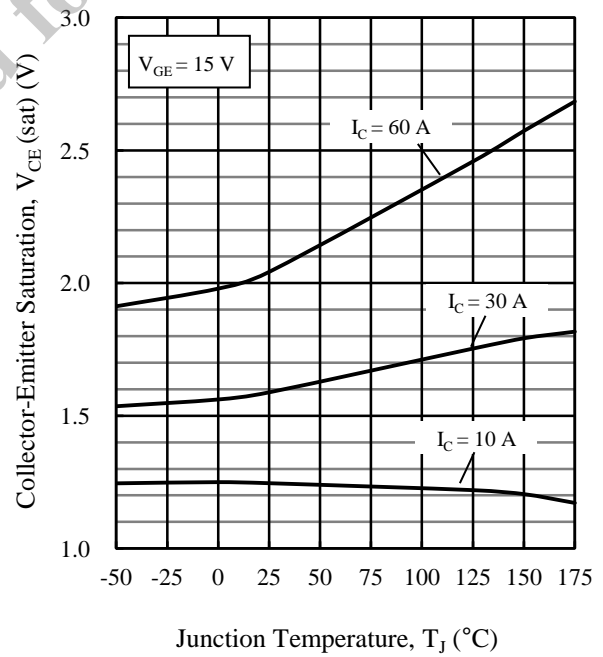


Figure 9. Saturation Voltage vs. Junction Temperature

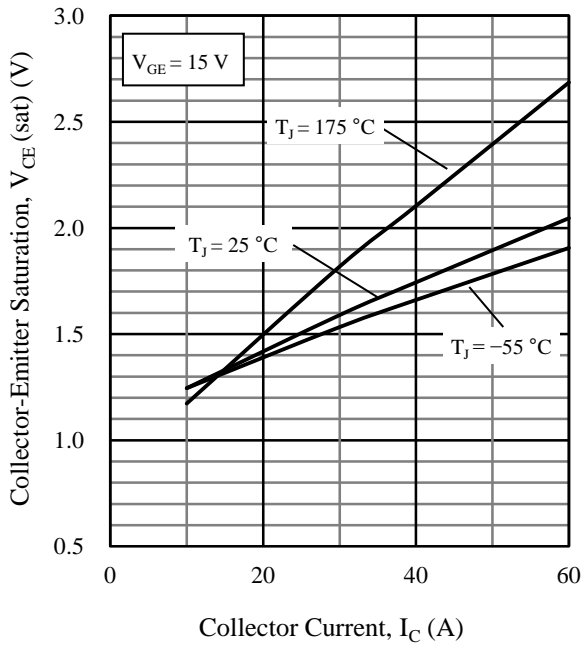


Figure 10. Saturation Voltage vs. Collector Current

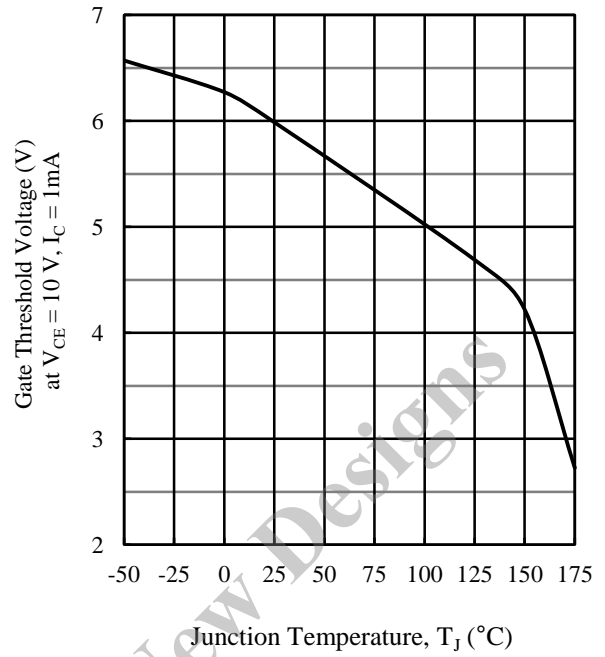


Figure 11. Gate Threshold Voltage vs. Junction Temperature

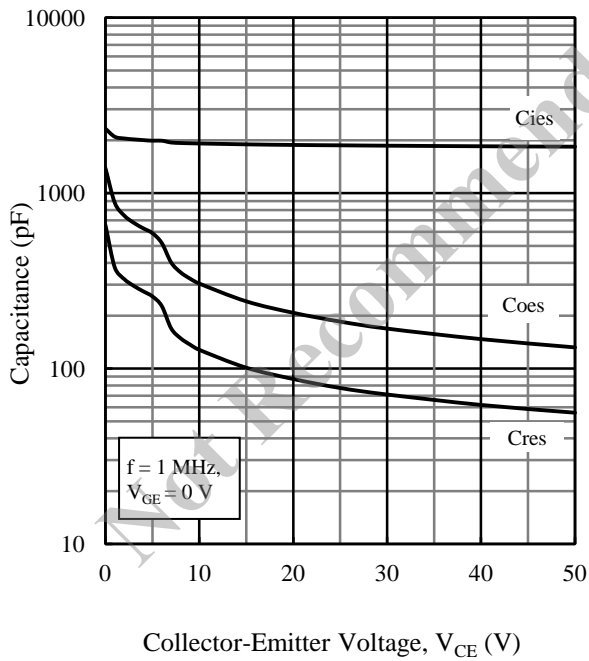


Figure 12. Capacitance Characteristics

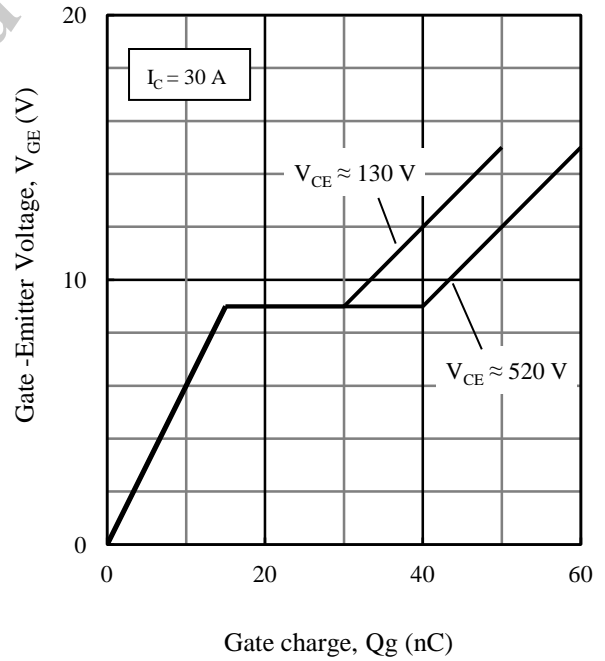


Figure 13. Typical Gate Charge

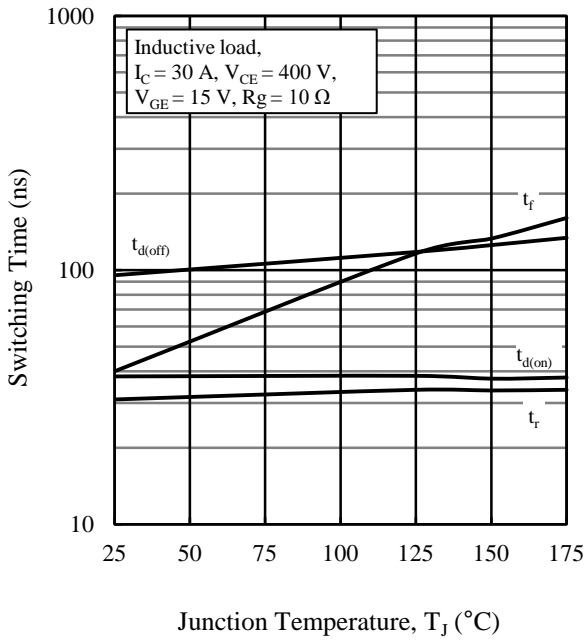


Figure 14. Switching Time vs. Junction Temperature

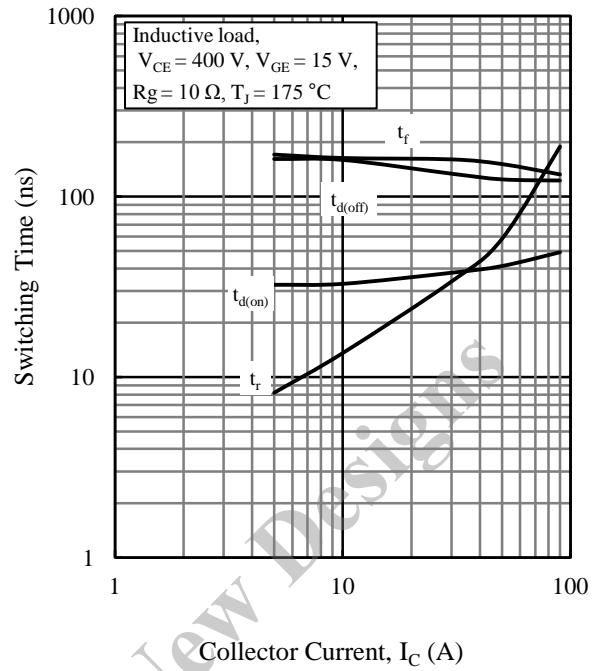


Figure 15. Switching Time vs. Collector Current

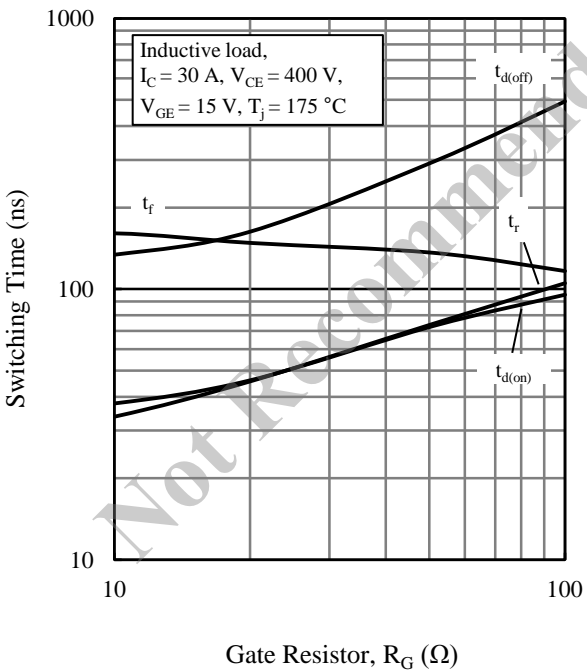


Figure 16. Switching Time vs. Gate Resistor

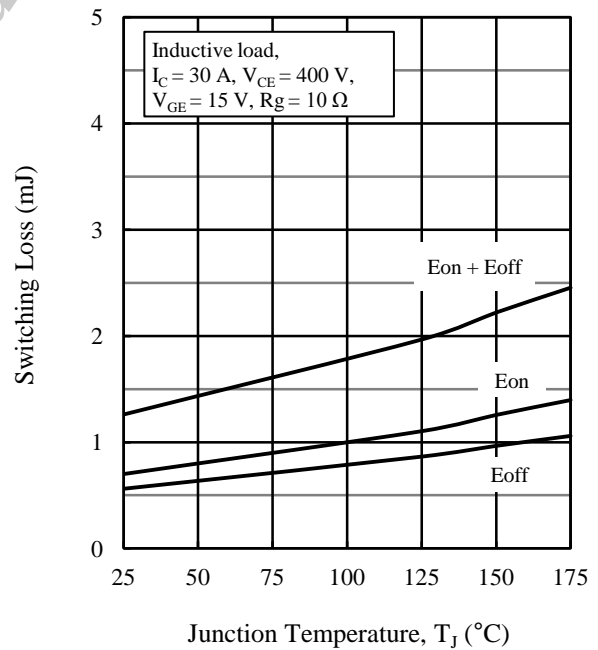


Figure 17. Switching Loss vs. Junction Temperature

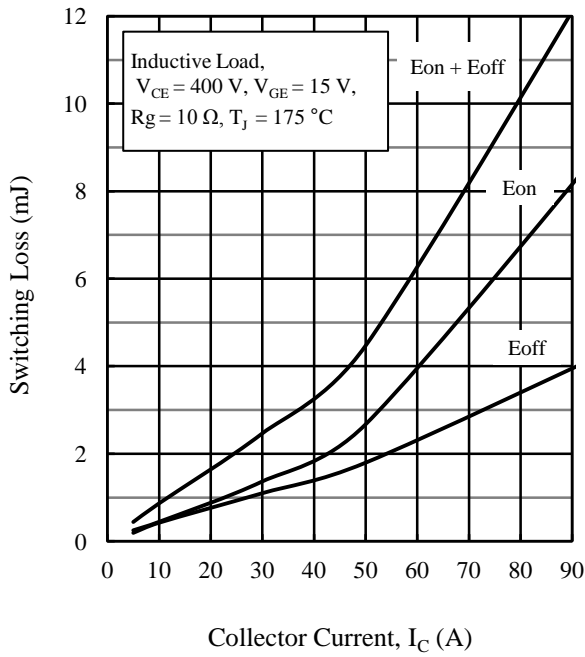


Figure 18. Switching Loss vs. Collector Current

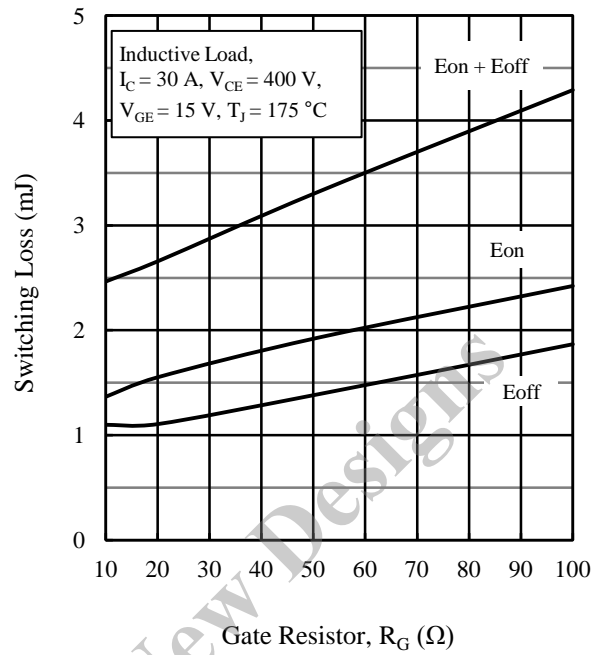


Figure 19. Switching Loss vs. Gate Resistor

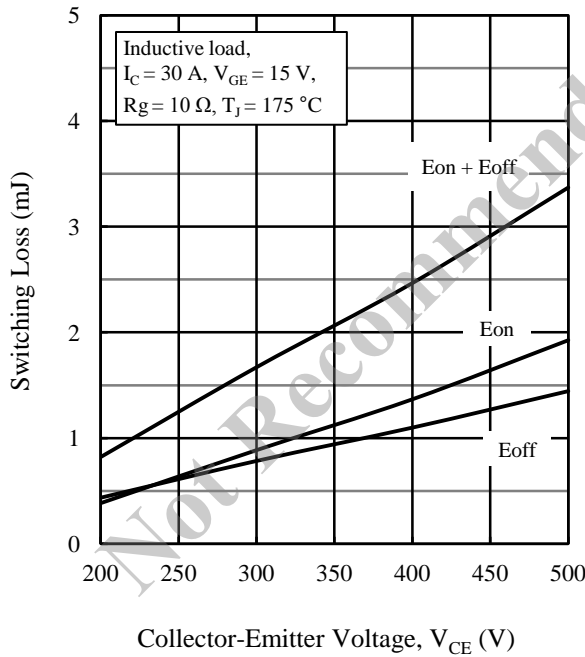


Figure 20. Switching Loss vs. Collector-Emitter Voltage

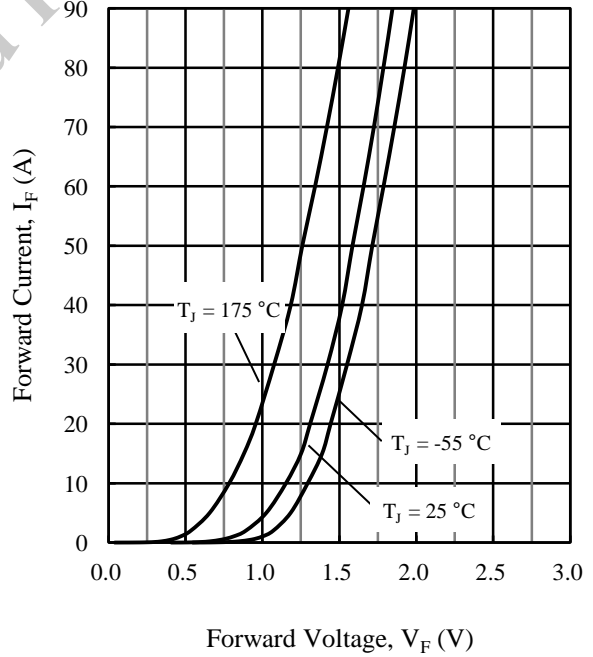


Figure 21. Diode Forward Characteristics

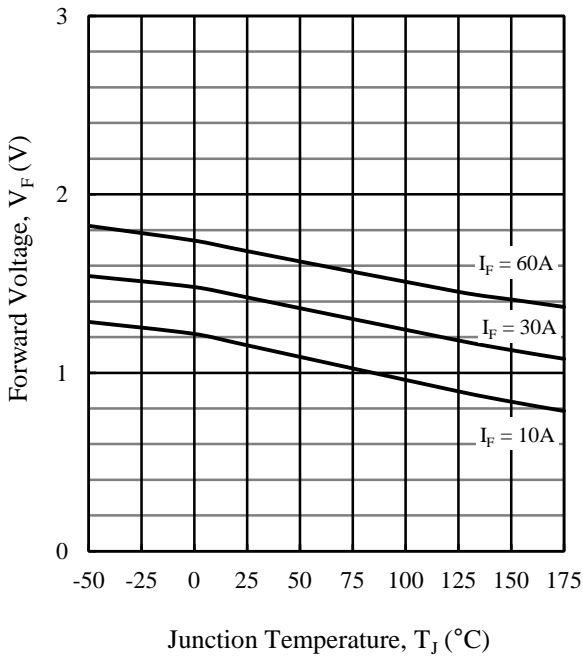


Figure 22. Diode Forward Voltage vs. Junction Temperature

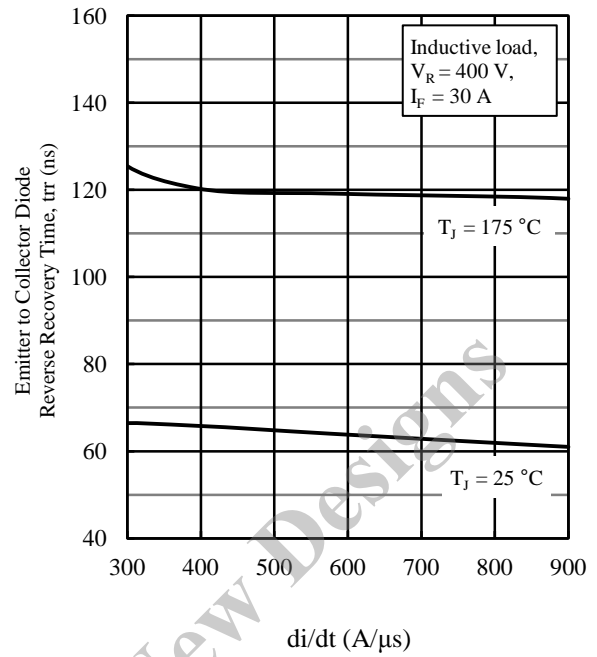


Figure 23. Emitter to Collector Diode Reverse Recovery Time vs. di/dt

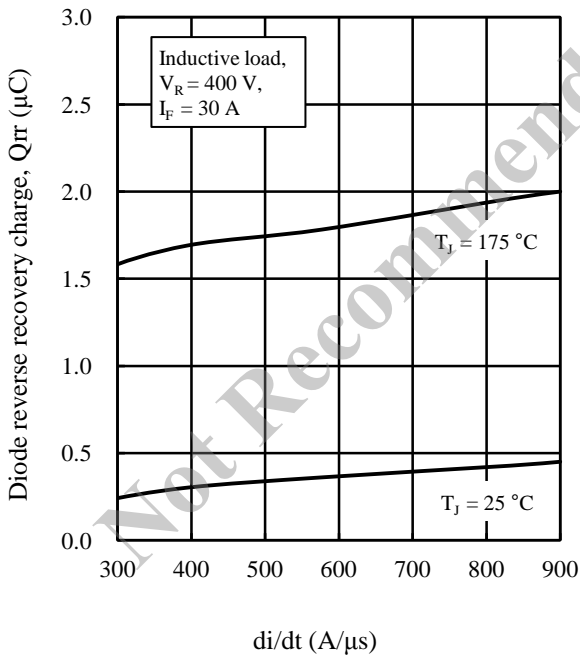


Figure 24. Diode Reverse Recovery Charge vs. di/dt

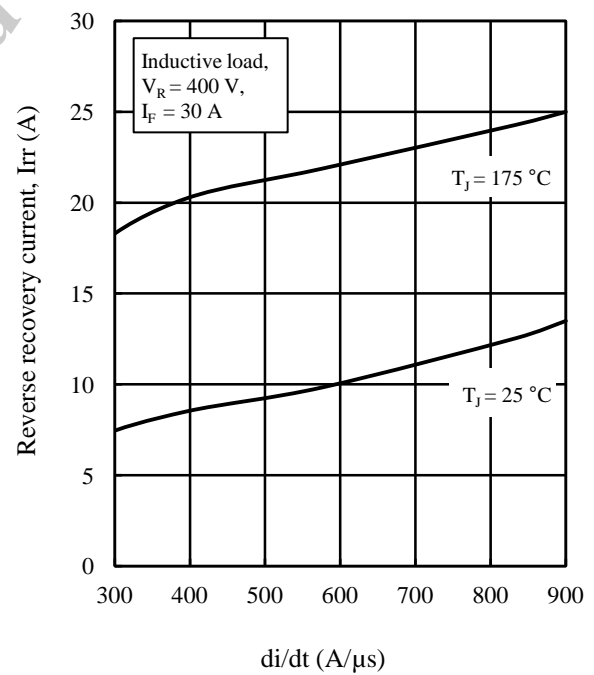


Figure 25. Recovery Current vs. di/dt

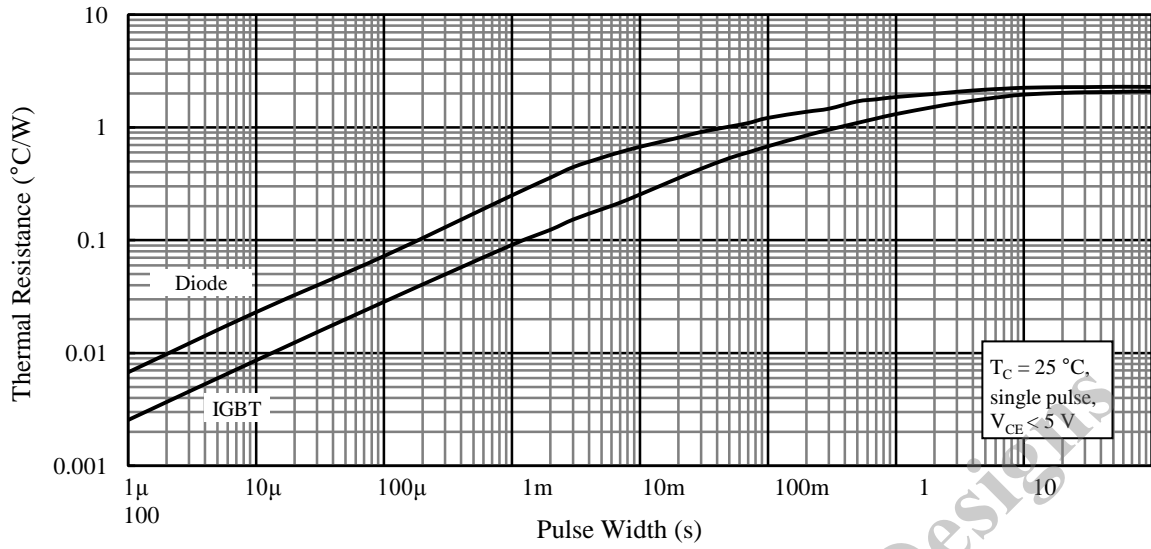


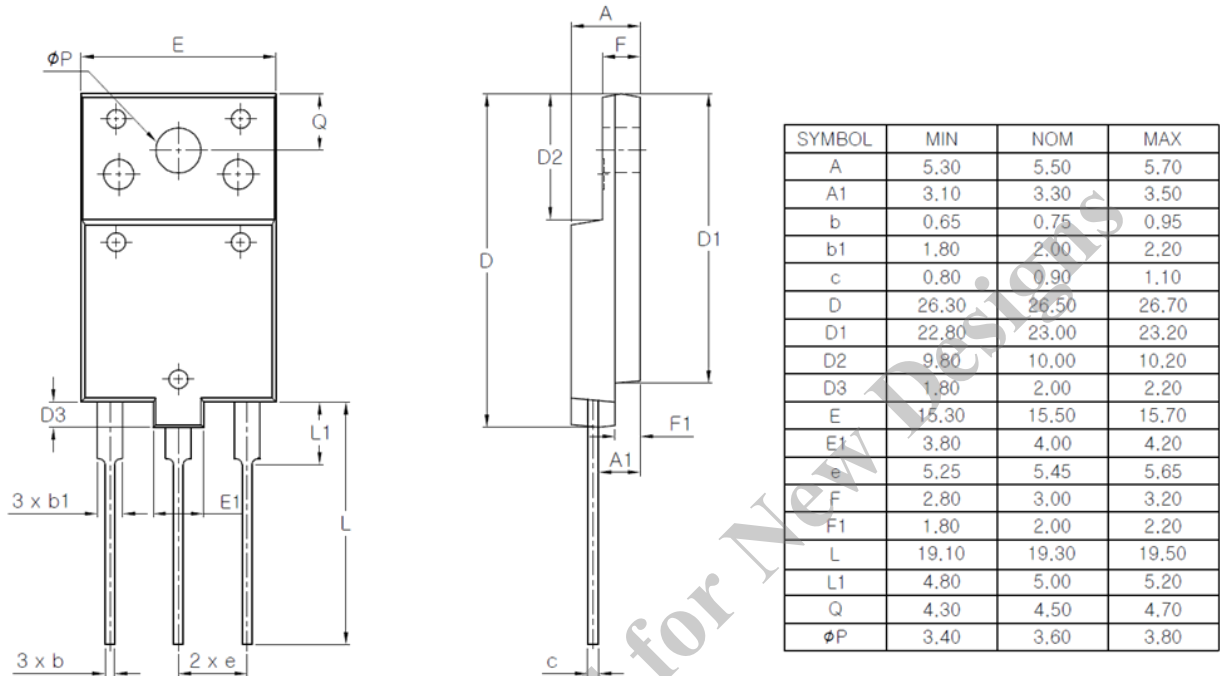
Figure 26. Transient Thermal Resistance

Not Recommended for New Design

FGF65A3L6L

Physical Dimensions

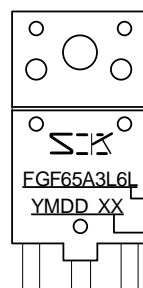
• TO3PF-3L



NOTES:

- Dimensions in millimeters
- Bare lead frame: Pb-free (RoHS compliant)
- When soldering the products, it is required to minimize the working time, within the following limits:
 Flow: $260 \pm 5 \text{ }^\circ\text{C} / 10 \pm 1 \text{ s}$, 2 times
 Soldering Iron: $380 \pm 10 \text{ }^\circ\text{C} / 3.5 \pm 0.5 \text{ s}$, 1 time (Soldering should be at a distance of at least 1.5 mm from the body of the product.)
- Recommended screw torque for TO3PF: 0.686 N·m to 0.882 N·m (7 kgf·cm to 9 kgf·cm)

Marking Diagram



Part Number

Lot Number:

Y is the last digit of the year of manufacture (0 to 9)

M is the month of the year (1 to 9, O, N, or D)

DD is the day of the month (01 to 31)

X is the control number

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